

STRUCTURE AND METHOD FOR SILICIDED METAL GATE TRANSISTORS

Abstract

A structure and method are provided for fabricating a field effect transistor (FET) having a metal gate structure. A metal gate structure is formed in an opening within a dielectric region formerly occupied by a sacrificial gate. The metal gate structure includes a first layer contacting a gate dielectric formed over a semiconductor region of a substrate. The first layer includes a material selected from the group consisting of metals and metal compounds. The gate further includes a silicide formed over the first layer. The FET further includes a source region and a drain region formed on opposite sides of the gate, the source and drain regions being silicided after the first layer of the gate is formed.